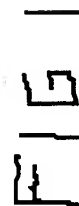


Inventor: Paul David Ranucci
Atty. Docket No.: P05767

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METAL OXIDE SEMICONDUCTOR (MOS)
BANDGAP VOLTAGE REFERENCE
CIRCUIT

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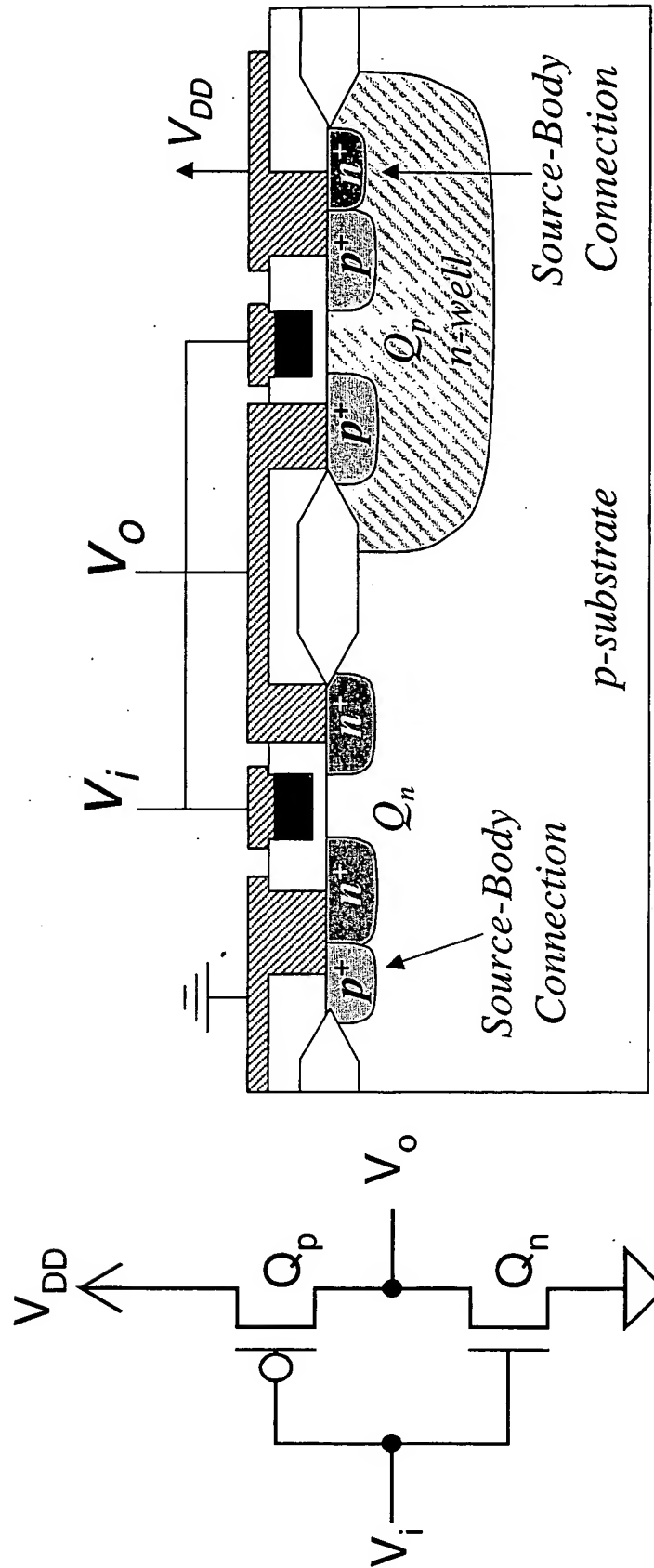
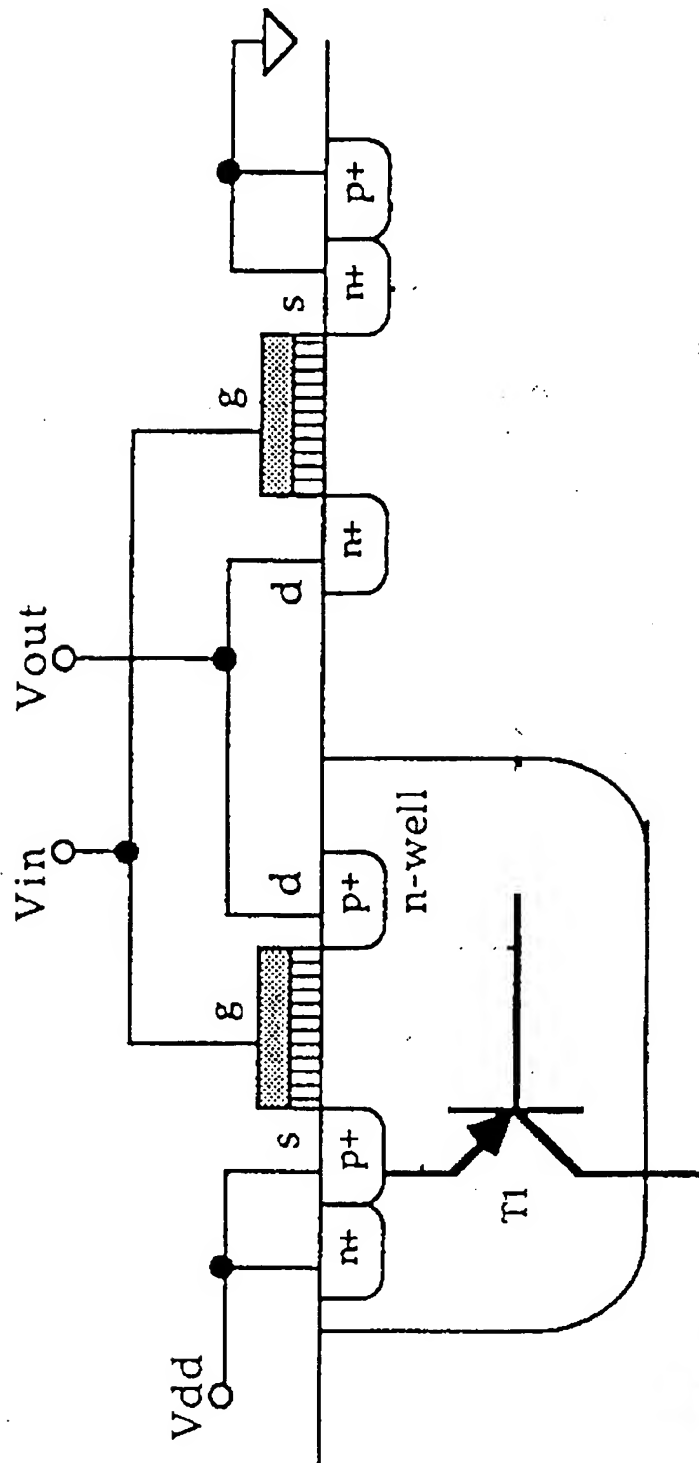


FIG 1A

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p-type substrate



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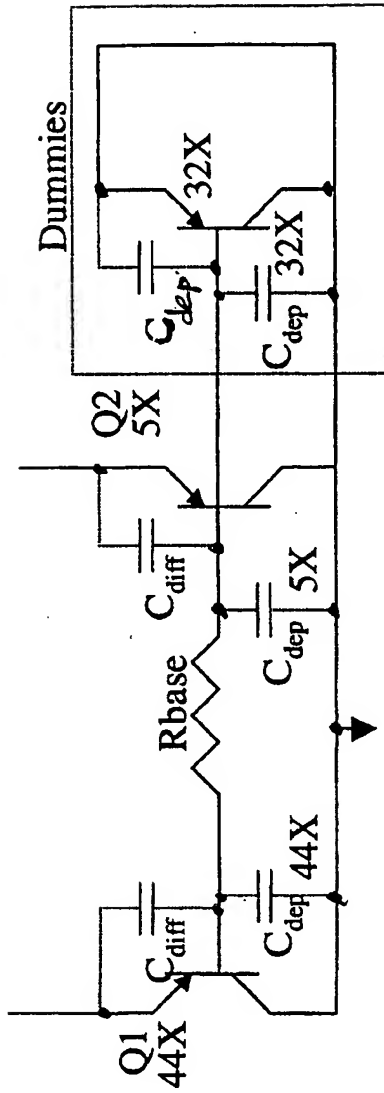


FIG 1

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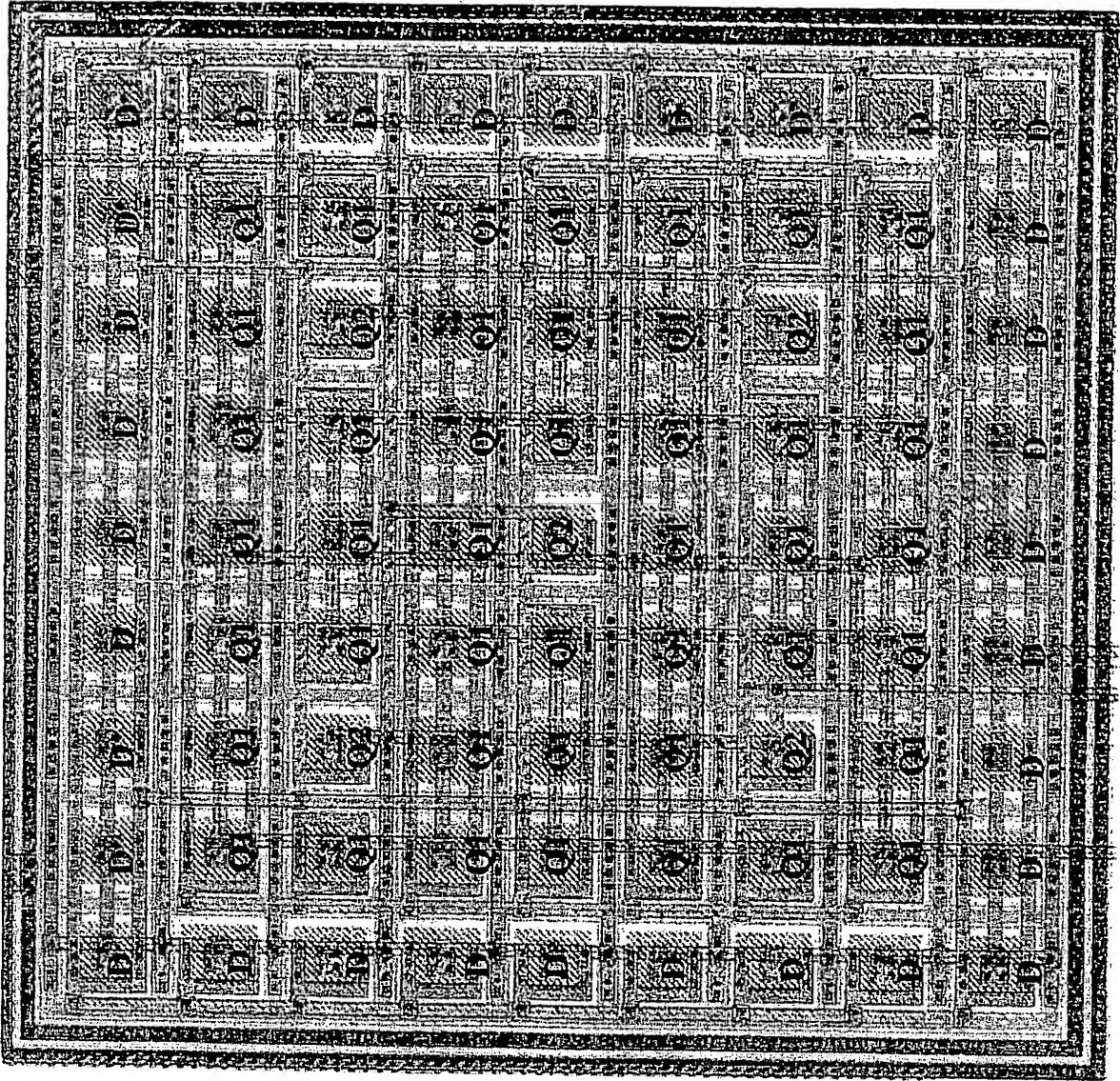


FIG 3

METAL OXIDE SEMICONDUCTOR (MOS)
BANDGAP VOLTAGE REFERENCE
CIRCUIT

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Atty. Docket No.: P05767

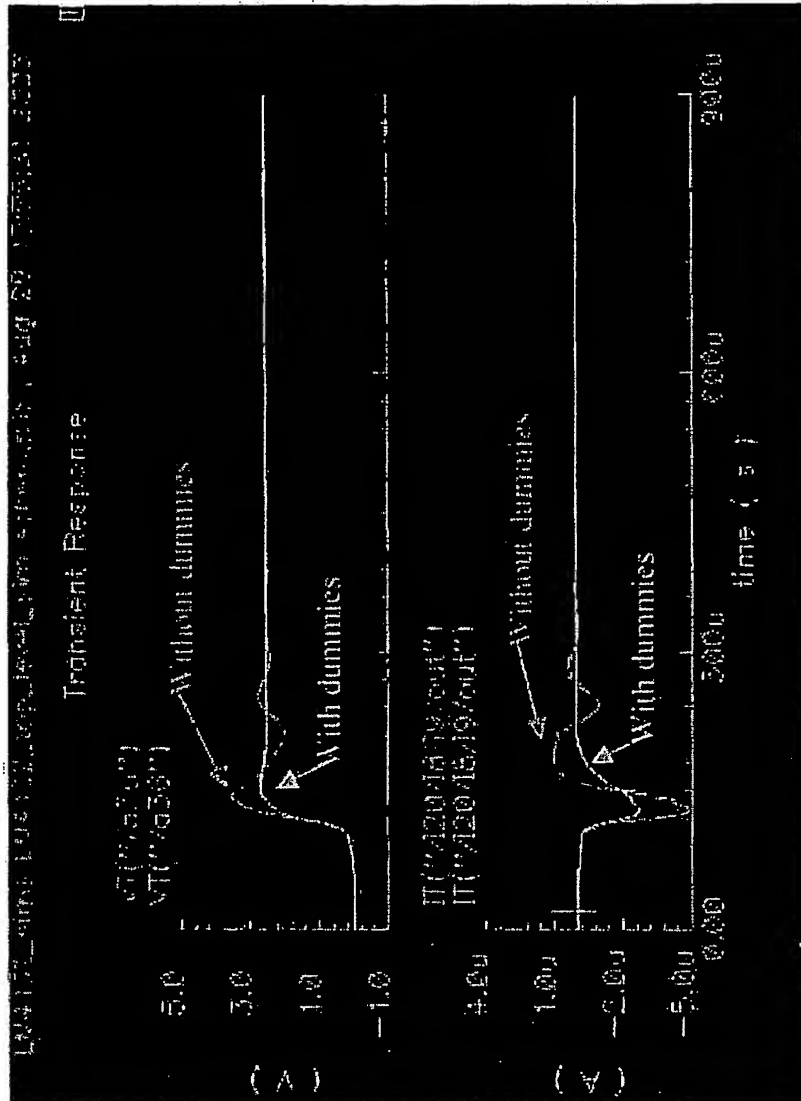


FIG 4